

### **TPS54627**

ZHCSBN2A - APRIL 2013 - REVISED SEPTEMBER 2013

4.5V 至 18V 输入, 6A 同步降压转换器

查询样品: TPS54627

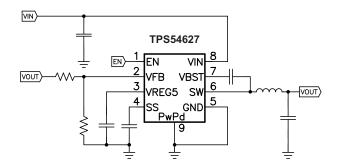
### 特性

#### 说明

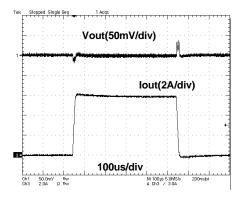
- D-CAP2™ 模式支持快速瞬态响应
- 低输出纹波,支持陶瓷输出电容器
- 宽 V<sub>IN</sub> 输入电压范围: 4.5V 至 18V
- 输出电压范围: 0.76V 至 5.5V
- 高效率集成型场效应晶体管 (FET) 针对较低占空比应用进行了优化
   - 36mΩ(高侧)与 28mΩ(低侧)
- 高效率,关断时流耗少于 10µA
- 高初始带隙基准精度
- 可调软启动
- 预偏置软启动
- 650kHz 开关频率 (f<sub>sw</sub>)
- 逐周期过流限制

### 应用范围

- 低电压系统的广泛应用
  - 数字电视电源
  - 高清 Blu-ray Disc<sup>™</sup> 播放器
  - 网络家庭终端设备
  - 数字机顶盒 (STB)



TPS54627 是一款自适应接通时间 D-CAP2™ 模式同 步降压转换器。TPS54627 可帮助系统设计人员通过 一个成本有效、低组件数量、低待机电流解决方案来完 成多种终端设备的电源总线调节器集。TPS54627 的 主控制环路使用 D-CAP2™ 模式控制,此控制方式在 无需外部补偿组件的情况下提供快速瞬态响应。 TPS54627 的专有电路还使该器件可采用诸如高分子 有机半导体固体电容器 (POSCAP) 或高分子聚合物电 容器 (SP-CAP) 等低等效串联电阻 (ESR) 输出电容 器,以及超低 ESR 陶瓷电容器。该器件的工作输入电 压介于 4.5V 至 18V VIN 之间。输出电压可在 0.76V 与 5.5V 之间进行设定。该器件还特有一个可调软启动 时间。TPS54627 采用 8 引脚 DDA 封装,并针对在 -40°C 到 85°C 的工作温度范围内的运行而设计。



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Blu-ray Disc is a trademark of Blu-ray Disc Association.

# **TPS54627**

ZHCSBN2A-APRIL 2013-REVISED SEPTEMBER 2013

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam

RUMENTS

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ORDERING INFORMATION<sup>(1)</sup>

| T <sub>A</sub> | PACKAGE <sup>(2) (3)</sup> | ORDERABLE PART NUMBER | PIN | TRANSPORT<br>MEDIA |
|----------------|----------------------------|-----------------------|-----|--------------------|
| 40%C to 95%C   |                            | TPS54627DDA           | 0   | Tube               |
| –40°C to 85°C  | DDA                        | TPS54627DDAR          | 0   | Tape and Reel      |

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

during storage or handling to prevent electrostatic damage to the MOS gates.

(3) All package options have Cu NIPDAU lead/ball finish.

### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

|                                       |                            | VA   | VALUE |      |  |
|---------------------------------------|----------------------------|------|-------|------|--|
|                                       |                            | MIN  | MAX   | UNIT |  |
|                                       | VIN, EN                    | -0.3 | 20    |      |  |
|                                       | VBST                       | -0.3 | 26    |      |  |
|                                       | VBST (10 ns transient)     | -0.3 | 28    |      |  |
| Input voltage range                   | VBST (vs SW)               | -0.3 | 6.5   | V    |  |
|                                       | VFB, SS                    | -0.3 | 6.5   |      |  |
|                                       | SW                         | -2   | 20    |      |  |
|                                       | SW (10 ns transient)       | -3   | 22    |      |  |
|                                       | VREG5                      | -0.3 | 6.5   | V    |  |
| Output voltage range                  | GND                        | -0.3 | 0.3   | V    |  |
| Voltage from GND to thermal           | pad, V <sub>diff</sub>     | -0.2 | 0.2   | V    |  |
| Electrostatio discharge               | Human Body Model (HBM)     |      | 2     | kV   |  |
| Electrostatic discharge               | Charged Device Model (CDM) |      | 500   | V    |  |
| Operating junction temperature        | e, T <sub>J</sub>          | -40  | 150   | °C   |  |
| Storage temperature, T <sub>stg</sub> |                            | -55  | 150   |      |  |

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### THERMAL INFORMATION

|                    | THERMAL METRIC <sup>(1)</sup>                | TPS54627     |                |
|--------------------|--|--------------|----------------|
|                    |  | DDA (8 PINS) | UNITS          |
| $\theta_{JA}$      | Junction-to-ambient thermal resistance       | 43.5         |                |
| θ <sub>JCtop</sub> | Junction-to-case (top) thermal resistance    | 49.4         |                |
| $\theta_{JB}$      | Junction-to-board thermal resistance         | 25.6         | 8 <b>0</b> AA4 |
| Ψ <sub>JT</sub>    | Junction-to-top characterization parameter   | 7.4          | °C/W           |
| $\Psi_{JB}$        | Junction-to-board characterization parameter | 25.5         |                |
| θ <sub>JCbot</sub> | Junction-to-case (bottom) thermal resistance | 5.2          |                |

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



### **RECOMMENDED OPERATING CONDITIONS**

over operating free-air temperature range, (unless otherwise noted)

|                 |                                |                        | MIN  | MAX | UNIT |
|-----------------|--------------------------------|------------------------|------|-----|------|
| V <sub>IN</sub> | Supply input voltage range     |                        | 4.5  | 18  | V    |
|                 |                                | VBST                   | -0.1 | 24  |      |
|                 |                                | VBST (10 ns transient) | -0.1 | 27  |      |
|                 |                                | VBST(vs SW)            | -0.1 | 6.0 |      |
|                 |                                | SS                     | -0.1 | 5.7 |      |
| VI              | Input voltage range            | EN                     | -0.1 | 18  | V    |
|                 |                                | VFB                    | -0.1 | 5.5 |      |
|                 |                                | SW                     | -1.8 | 18  |      |
|                 |                                | SW (10 ns transient)   | -3   | 21  |      |
|                 |                                | GND                    | -0.1 | 0.1 |      |
| Vo              | Output voltage range           | VREG5                  | -0.1 | 5.7 | V    |
| lo              | Output Current range           | I <sub>VREG5</sub>     | 0    | 5   | mA   |
| T <sub>A</sub>  | Operating free-air temperature | · · · ·                | -40  | 85  | °C   |
| TJ              | Operating junction temperature |                        | -40  | 150 | °C   |

### **ELECTRICAL CHARACTERISTICS**

over operating free-air temperature range,  $V_{\text{IN}}$  = 12 V (unless otherwise noted)

|                        | PARAMETER                                | TEST CONDITIONS   | MIN | TYP | MAX   | UNIT |
|------------------------|--|---|-----|-----|-------|------|
| SUPPLY CU              | RRENT                                    |   |     |     |       |      |
| I <sub>VIN</sub>       | Operating - non-switching supply current | $V_{IN}$ current, $T_A = 25^{\circ}C$ , EN = 5 V,<br>$V_{FB} = 0.8$ V         |     | 950 | 1400  | μΑ   |
| I <sub>VINSDN</sub>    | Shutdown supply current                  | $V_{IN}$ current, $T_A = 25^{\circ}C$ , $EN = 0 V$                            |     | 3   | 10    | μA   |
| LOGIC THRE             | ESHOLD                                   |   |     |     |       |      |
|                        | EN high-level input voltage              | EN  | 1.6 |     |       | V    |
| V <sub>EN</sub>        | EN low-level input voltage               | EN  |     |     | 0.6   | V    |
| R <sub>EN</sub>        | EN pin resistance to GND                 | V <sub>EN</sub> = 12 V  | 200 | 400 | 800   | kΩ   |
| V <sub>FB</sub> VOLTAG | SE AND DISCHARGE RESISTANCE              |   | •   |     |       |      |
|                        | M. danseled as the sec                   | $T_A = 25^{\circ}C$ , $V_O = 1.05$ V, continuous mode operation               | 757 | 765 | 773   | mV   |
| V <sub>FBTH</sub>      | V <sub>FB</sub> threshold voltage        | $T_A = -40$ to 85°C, $V_O = 1.05$ V, continuous mode operation <sup>(1)</sup> | 751 | 765 | 779   | mV   |
| I <sub>VFB</sub>       | V <sub>FB</sub> input current            | V <sub>FB</sub> = 0.8 V, T <sub>A</sub> = 25°C                                |     | 0   | ±0.15 | μA   |
| V <sub>REG5</sub> OUTP | UT                                       |   | •   |     |       |      |
| V <sub>VREG5</sub>     | V <sub>REG5</sub> output voltage         | $T_A = 25^{\circ}C, 6.0 V < V_{IN} < 18 V, 0 < I_{VREG5} < 5 mA$              | 5.2 | 5.5 | 5.7   | V    |
| I <sub>VREG5</sub>     | Output current                           | $V_{IN} = 6 \text{ V}, V_{REG5} = 4.0 \text{ V}, T_A = 25^{\circ}\text{C}$    | 20  |     |       | mA   |
| VOUT DISCH             | ARGE                                     |   |     |     |       |      |
| R <sub>DISCHG</sub>    | V <sub>OUT</sub> discharge resistance    | EN = 0 V, SW = 0.5 V, T <sub>A</sub> = 25°C                                   |     | 500 | 800   | Ω    |
| MOSFET                 | +  | •   |     |     |       |      |
|                        | High side switch resistance              | 25°C, V <sub>BST</sub> - SW = 5.5 V   |     | 36  |       | mΩ   |
| R <sub>DS(on)</sub>    | Low side switch resistance               | 25°C  |     | 28  |       | mΩ   |
| CURRENT L              | IMIT                                     | ,   | 1   |     |       |      |
| I <sub>OCL</sub>       | Current limit                            | L out = 1.5 µH <sup>(1)</sup>   | 6.7 | 7.3 | 8.9   | А    |

(1) Not production tested.

**TPS54627** 

ZHCSBN2A - APRIL 2013 - REVISED SEPTEMBER 2013

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# **ELECTRICAL CHARACTERISTICS (continued)**

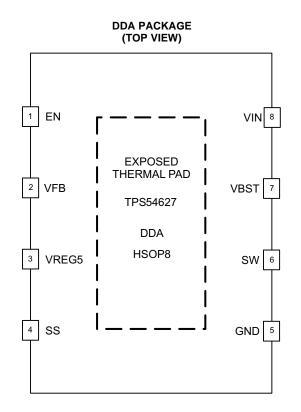
over operating free-air temperature range,  $V_{\text{IN}}$  = 12 V (unless otherwise noted)

|                       | PARAMETER                  | TEST CONDITIONS                                 | MIN    | TYP  | MAX  | UNIT |
|-----------------------|----------------------------|---|--------|------|------|------|
| THERMAL SHUT          | DOWN                       |   |        |      |      |      |
| Ŧ                     |                            | Shutdown temperature <sup>(2)</sup>             |        | 165  |      | °C   |
| T <sub>SDN</sub>      | Thermal shutdown threshold | Hysteresis <sup>(2)</sup>                       |        | 35   |      | Ĵ    |
| ON-TIME TIMER         | CONTROL                    |   | u.     |      |      |      |
| t <sub>ON</sub>       | On time                    | V <sub>IN</sub> = 12 V, V <sub>O</sub> = 1.05 V |        | 150  |      | ns   |
| t <sub>OFF(MIN)</sub> | Minimum off time           | $T_A = 25^{\circ}C, V_{FB} = 0.7 V$             |        | 260  | 310  | ns   |
| SOFT START            |                            |   |        |      | ·    |      |
|                       | SS charge current          | V <sub>SS</sub> = 1 V                           | 4.2    | 6    | 7.8  | μA   |
| I <sub>SS</sub>       | SS discharge current       | V <sub>SS</sub> = 0.5 V                         | 1.5    | 3.3  |      | mA   |
| HICCUP AND OV         | ER-VOLTAGE PROTECTION      |   |        |      |      |      |
| V <sub>OVP</sub>      | Output OVP threshold       | OVP Detect (L > H)                              |        | 125% |      |      |
| VHICCUP               | Output Hiccup threshold    | Hiccup detect (H > L)                           |        | 65%  |      |      |
| THICCUPDELAY          | Output Hiccup delay        | To hiccup state                                 |        | 250  |      | µsec |
| THICCUPENDELAY        | Output Hiccup Enable delay | Relative to soft-start time                     |        | x1.7 |      |      |
| UVLO                  |                            |   |        |      |      |      |
|                       | LIV/LO threehold           | Wake up V <sub>REG5</sub> voltage 3.45          |        | 3.75 | 4.05 | V    |
| UVLO                  | UVLO threshold             | Hysteresis V <sub>REG5</sub> voltage            | 0.13 ( |      |      | V    |

(2) Not production tested.

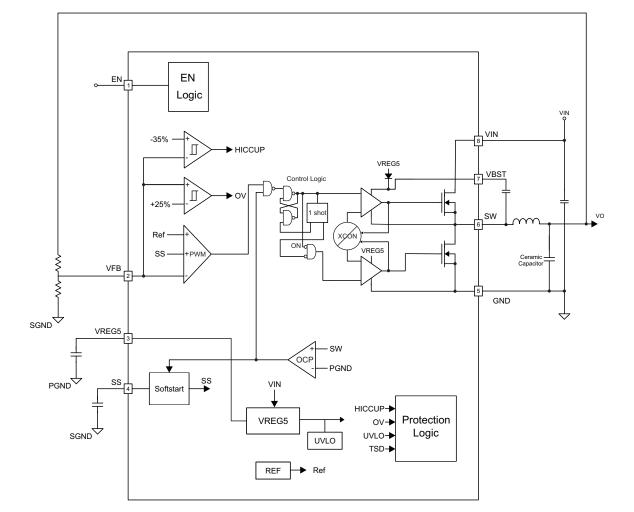


### **DEVICE INFORMATION**



#### **PIN FUNCTIONS**

| PIN                    |           |   |  |  |  |  |  |
|------------------------|-----------|---|--|--|--|--|--|
| NAME                   | NO.       | DESCRIPTION   |  |  |  |  |  |
| EN                     | 1         | Enable input control. EN is active high and must be pulled up to enable the device.   |  |  |  |  |  |
| VFB                    | 2         | Converter feedback input. Connect to output voltage with feedback resistor divider.   |  |  |  |  |  |
| VREG5                  | 3         | 5.5 V power supply output. A capacitor (typical 1 $\mu F)$ should be connected to GND. VREG5 is not active when EN is low.                                      |  |  |  |  |  |
| SS                     | 4         | Soft-start control. An external capacitor should be connected to GND.   |  |  |  |  |  |
| GND                    | 5         | Ground pin. Power ground return for switching circuit. Connect sensitive SS and VFB returns to GND at a single point.   |  |  |  |  |  |
| SW                     | 6         | Switch node connection between high-side NFET and low-side NFET.  |  |  |  |  |  |
| VBST                   | 7         | Supply input for the high-side FET gate drive circuit. Connect 0.1µF capacitor between VBST and SW pins. An internal diode is connected between VREG5 and VBST. |  |  |  |  |  |
| VIN                    | 8         | Input voltage supply pin.   |  |  |  |  |  |
| Exposed Thermal<br>Pad | Back side | Thermal pad of the package. Must be soldered to achieve appropriate dissipation. Must be connected to GND.  |  |  |  |  |  |



#### FUNCTIONAL BLOCK DIAGRAM



TEXAS INSTRUMENTS

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#### **OVERVIEW**

The TPS54627 is a 6-A synchronous step-down (buck) converter with two integrated N-channel MOSFETs. It operates using D-CAP2<sup>™</sup> mode control. The fast transient response of D-CAP2<sup>™</sup> control reduces the output capacitance required to meet a specific level of performance. Proprietary internal circuitry allows the use of low ESR output capacitors including ceramic and special polymer types.

#### **DETAILED DESCRIPTION**

#### **PWM Operation**

The main control loop of the TPS54627 is an adaptive on-time pulse width modulation (PWM) controller that supports a proprietary D-CAP2<sup>™</sup> mode control. D-CAP2<sup>™</sup> mode control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output.

At the beginning of each cycle, the high-side MOSFET is turned on. This MOSFET is turned off after internal one shot timer expires. This one shot is set by the converter input voltage, VIN, and the output voltage, VO, to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The one-shot timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the reference voltage. An internal ramp is added to reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2<sup>™</sup> mode control.

#### **PWM Frequency and Adaptive On-Time Control**

TPS54627 uses an adaptive on-time control scheme and does not have a dedicated on board oscillator. The TPS54627 runs with a pseudo-constant frequency of 650 kHz by using the input voltage and output voltage to set the on-time one-shot timer. The on-time is inversely proportional to the input voltage and proportional to the output voltage; therefore, when the duty ratio is VOUT/VIN, the frequency is constant.

#### Soft Start and Pre-Biased Soft Start

The soft start function is adjustable. When the EN pin becomes high,  $6\mu$ A current begins charging the capacitor which is connected from the SS pin to GND. Smooth control of the output voltage is maintained during start up. The equation for the slow start time is shown in Equation 1. VFB voltage is 0.765 V and SS pin source current is  $6\mu$ A.

$$t_{ss}(ms) = \frac{C6(nF) \times V_{FB} \times 1.1}{I_{ss}(\mu A)} = \frac{C6(nF) \times 0.765 \times 1.1}{6}$$
(1)

The TPS54627 contains a unique circuit to prevent current from being pulled from the output during startup if the output is pre-biased. When the soft-start commands a voltage higher than the pre-bias level (internal soft start becomes greater than feedback voltage  $V_{FB}$ ), the controller slowly activates synchronous rectification by starting the first low side FET gate driver pulses with a narrow on-time. It then increments that on-time on a cycle-by-cycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-bias output, and ensure that the out voltage ( $V_O$ ) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation.

#### Output Discharge Control

TPS54627 discharges the output when EN is low, or the controller is turned off by the UVLO protection. The internal low-side MOSFET is not turned on for the output discharge operation to avoid the possibility of causing negative voltage at the output.

#### **Current Protection**

The output overcurrent protection (OCP) is implemented using a cycle-by-cycle valley detect control circuit. The switch current is monitored by measuring the low-side FET switch voltage between the SW pin and GND. This voltage is proportional to the switch current. To improve accuracy, the voltage sensing is temperature compensated.

**TPS54627** 

ZHCSBN2A - APRIL 2013-REVISED SEPTEMBER 2013



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During the on time of the high-side FET switch, the switch current increases at a linear rate determined by  $V_{IN}$ ,  $V_{OUT}$ , the on-time and the output inductor value. During the on time of the low-side FET switch, this current decreases linearly. The average value of the switch current is the load current  $I_{OUT}$ . The TPS54627 constantly monitors the low-side FET switch voltage, which is proportional to the switch current, during the low-side on-time. If the measured voltage is above the voltage proportional to the current limit, an internal counter is incremented per each SW cycle and the converter maintains the low-side switch on until the measured voltage is below the voltage corresponding to the current limit at which time the switching cycle is terminated and a new switching cycle begins. In subsequent switching cycles, the on-time is set to a fixed value and the current is monitored in the same manner. If the over current condition exists for 7 consecutive switching cycles, the internal OCL threshold is set to a lower level, reducing the available output current. When a switching cycle occurs where the switch current is not above the lower OCL threshold, the counter is reset and the OCL limit is returned to the higher value.

There are some important considerations for this type of over-current protection. The peak current is the average load current plus one half of the peak-to-peak inductor current. The valley current is the average load current minus one half of the peak-to-peak inductor current. Since the valley current is used to detect the over-current threshold, the load current is higher than the over-current threshold. Also, when the current is being limited, the output voltage tends to fall. When the VFB voltage becomes lower than 65% of the target voltage, the UVP comparator detects it. If the under-voltage condition persists for 250 µs, the device will shut down and re-start in hiccup mode after 7 times the SS period. When the over current condition is removed, the output voltage will return to the regulated value. This protection is non-latching.

#### **Over Voltage Protection**

TPS54627 detects over and under voltage conditions by monitoring the feedback voltage (VFB). This function is enabled after approximately 1.7 x times the soft start time. When the feedback voltage becomes higher than 125% of the target voltage, the OVP comparator output goes high and both the high-side MOSFET driver and the low-side MOSFET driver turn off. This function is non-latch operation.

#### **UVLO Protection**

Undervoltage lock out protection (UVLO) monitors the voltage of the  $V_{REG5}$  pin. When the  $V_{REG5}$  voltage is lower than UVLO threshold voltage, the TPS54627 is shut off. This protection is non-latching.

#### Thermal Shutdown

TPS54627 monitors the temperature of itself. If the temperature exceeds the threshold value (typically 165°C), the device is shut off. This is non-latch protection.

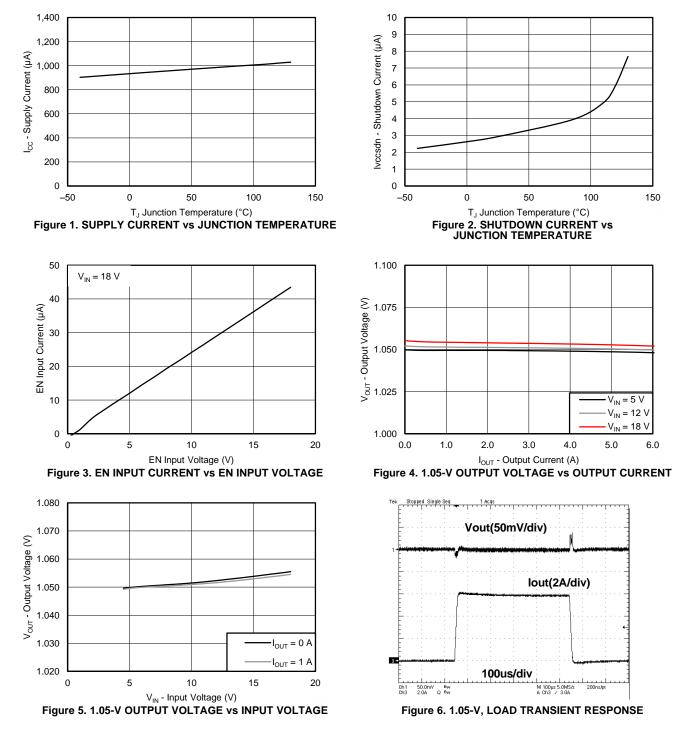


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#### **TYPICAL CHARACTERISTICS**

VIN = 12 V,  $T_A = 25^{\circ}C$  (unless otherwise noted).



# TPS54627

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Figure 11. VFB VOLTAGE vs JUNCTION TEMPERATURE

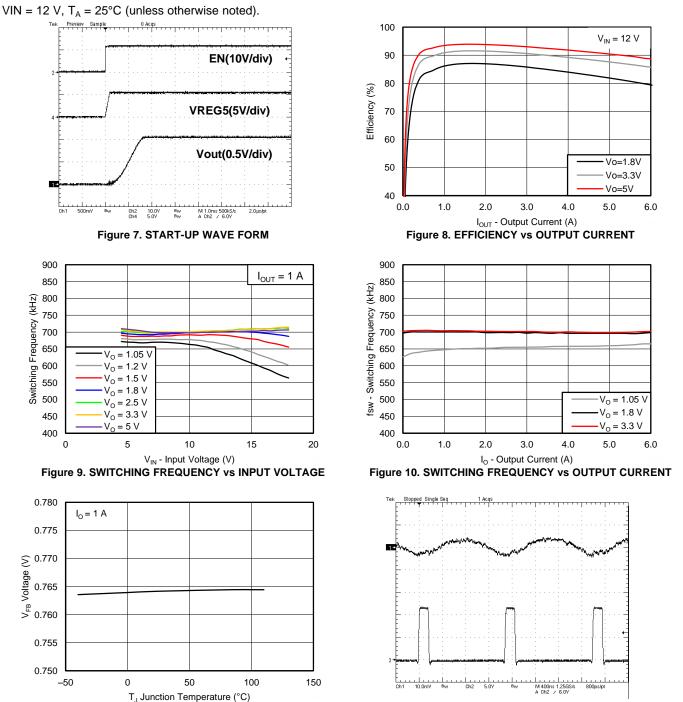


Figure 12. VOLTAGE RIPPLE AT OUTPUT (I<sub>O</sub> = 6 A)



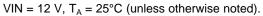
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### **TYPICAL CHARACTERISTICS (continued)**



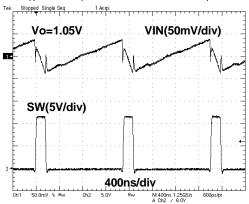
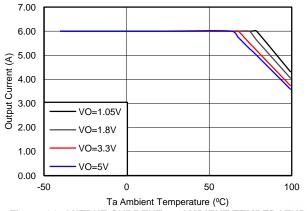


Figure 13. VOLTAGE RIPPLE AT INPUT (I<sub>O</sub> = 6 A)





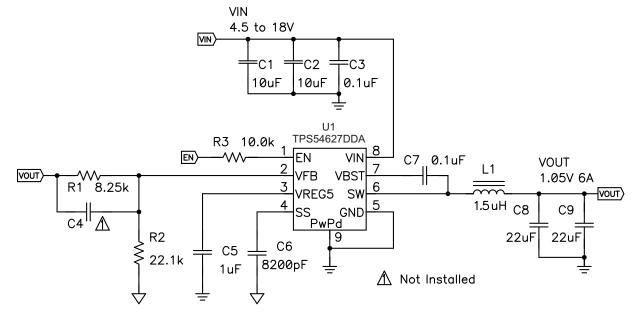
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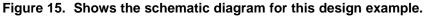
### **DESIGN GUIDE**

### Step-By-Step Design Procedure

To begin the design process, the user must know a few application parameters:

- Input voltage range
- Output voltage
- Output current
- Output voltage ripple
- Input voltage ripple





#### **Output Voltage Resistors Selection**

The output voltage is set with a resistor divider from the output node to the VFB pin. It is recommended to use 1% tolerance or better divider resistors. Start by using Equation 2 to calculate  $V_{OUT}$ .

To improve efficiency at light loads consider using larger value resistors, high resistance is more susceptible to noise, and the voltage errors from the VFB input current are more noticeable.

$$V_{OUT} = 0.765 \text{ x} \left(1 + \frac{\text{R1}}{\text{R2}}\right)$$

#### **Output Filter Selection**

12

The output filter used with the TPS54627 is an LC circuit. This LC filter has double pole at:

$$F_{P} = \frac{I}{2\pi \sqrt{L_{OUT} \times C_{OUT}}}$$

At low frequencies, the overall loop gain is set by the output set-point resistor divider network and the internal gain of the TPS54627. The low frequency phase is 180 degrees. At the output filter pole frequency, the gain rolls off at a -40 dB per decade rate and the phase drops rapidly. D-CAP2<sup>TM</sup> introduces a high frequency zero that reduces the gain roll off to -20 dB per decade and increases the phase to 90 degrees one decade above the zero frequency. The inductor and capacitor selected for the output filter must be selected so that the double pole of Equation 3 is located below the high frequency zero but close enough that the phase boost provided be the high frequency zero provides adequate phase margin for a stable circuit. To meet this requirement use the values recommended in Table 1

INSTRUMENTS

**EXAS** 

(2)

(3)

|                | Table 1. Recommended Component Values |         |     |                        |     |     |         |     |      |         |  |  |  |  |
|----------------|---------------------------------------|---------|-----|------------------------|-----|-----|---------|-----|------|---------|--|--|--|--|
| Output         |                                       |         |     | C4 (pF) <sup>(1)</sup> |     |     | L1 (µH) |     | C8 + | C9 (µF) |  |  |  |  |
| Voltage<br>(V) | R1 (kΩ)                               | R2 (kΩ) | MIN | ТҮР                    | MAX | MIN | ТҮР     | MAX | MIN  | MAX     |  |  |  |  |
| 1              | 6.81                                  | 22.1    | 5   | 150                    | 220 | 1.0 | 1.5     | 4.7 | 22   | 68      |  |  |  |  |
| 1.05           | 8.25                                  | 22.1    | 5   | 150                    | 220 | 1.0 | 1.5     | 4.7 | 22   | 68      |  |  |  |  |
| 1.2            | 12.7                                  | 22.1    | 5   |                        | 100 | 1.0 | 1.5     | 4.7 | 22   | 68      |  |  |  |  |
| 1.5            | 21.5                                  | 22.1    | 5   |                        | 68  | 1.0 | 1.5     | 4.7 | 22   | 68      |  |  |  |  |
| 1.8            | 30.1                                  | 22.1    | 5   |                        | 22  | 1.2 | 1.5     | 4.7 | 22   | 68      |  |  |  |  |
| 2.5            | 49.9                                  | 22.1    | 5   |                        | 22  | 1.5 | 2.2     | 4.7 | 22   | 68      |  |  |  |  |
| 3.3            | 73.2                                  | 22.1    | 2   |                        | 22  | 1.8 | 2.2     | 4.7 | 22   | 68      |  |  |  |  |
| 5              | 124                                   | 22.1    | 2   |                        | 22  | 2.2 | 3.3     | 4.7 | 22   | 68      |  |  |  |  |

### Table 1. Recommended Component Values

#### (1) Optional

Since the DC gain is dependent on the output voltage, the required inductor value increases as the output voltage increases. Additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1. The feed forward capacitor is most effective for output voltages at or above 1.8 V.

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using Equation 4, Equation 5 and Equation 6. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current. Use 650 kHz for  $f_{SW}$ .

Use 650 kHz for  $f_{SW}$ . Make sure the chosen inductor is rated for the peak current of Equation 5 and the RMS current of Equation 6.

$$I_{IPP} = \frac{V_{OUT}}{V_{IN(max)}} \times \frac{V_{IN(max)} - V_{OUT}}{L_{O} \times f_{SW}}$$

$$(4)$$

$$I_{\text{lpeak}} = I_{\text{O}} + \frac{1}{2}$$

$$I_{\text{Lo}(\text{RMS})} = \sqrt{I_{\text{O}}^2 + \frac{1}{12} I_{\text{IPP}}^2}$$
(5)
(6)

For this design example, the calculated peak current is 6.51 A and the calculated RMS current is 6.01 A. The inductor used is a TDK SPM6530-1R5M100 with a peak current rating of 11.5 A and an RMS current rating of 11 A.

The capacitor value and ESR determines the amount of output voltage ripple. The TPS54627 is intended for use with ceramic or other low ESR capacitors. Recommended values range from  $22\mu$ F to  $68\mu$ F. Use Equation 7 to determine the required RMS current rating for the output capacitor.

$$I_{Co(RMS)} = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{\sqrt{12} \times V_{IN} \times L_O \times f_{SW}}$$

For this design two TDK C3216X5R0J226M 22 $\mu$ F output capacitors are used. The typical ESR is 2 m $\Omega$  each. The calculated RMS current is 0.284 A and each output capacitor is rated for 4A.

#### Input Capacitor Selection

The TPS54627 requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A ceramic capacitor over 10  $\mu$ F is recommended for the decoupling capacitor. An additional 0.1  $\mu$ F capacitor (C3) from pin 8 to ground is optional to provide additional high frequency filtering. The capacitor voltage rating needs to be greater than the maximum input voltage.

#### **Bootstrap Capacitor Selection**

A 0.1  $\mu$ F. ceramic capacitor must be connected between the VBST to SW pin for proper operation. It is recommended to use a ceramic capacitor.

(7)

# **TPS54627**

ZHCSBN2A - APRIL 2013-REVISED SEPTEMBER 2013



#### **VREG5 Capacitor Selection**

A  $1-\mu F$ . ceramic capacitor must be connected between the VREG5 to GND pin for proper operation. It is recommended to use a ceramic capacitor.

### THERMAL INFORMATION

This 8-pin DDA package incorporates an exposed thermal pad that is designed to be directly to an external heartsick. The thermal pad must be soldered directly to the printed board (PCB). After soldering, the PCB can be used as a heartsick. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heartsick structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the exposed thermal pad and how to use the advantage of its heat dissipating abilities, see the Technical Brief, PowerPAD<sup>™</sup> Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD<sup>™</sup> Made Easy, Texas Instruments Literature No. SLMA004.

The exposed thermal pad dimensions for this package are shown in the following illustration.

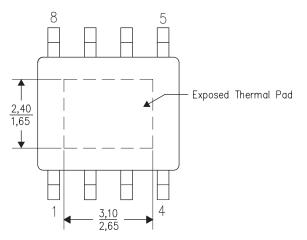
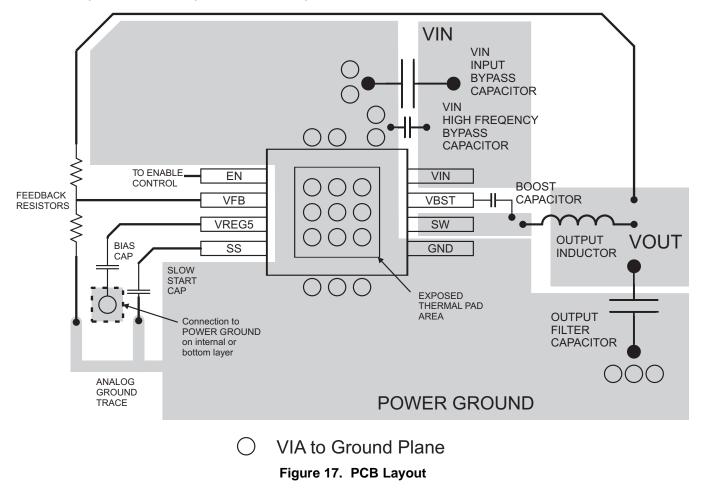


Figure 16. Thermal Pad Dimensions



#### LAYOUT CONSIDERATIONS

- 1. The TPS54627 can supply large load currents up to 6 A, so heat dissipation may be a concern. The top side area adjacent to the TPS54627 should be filled with ground as much as possible to dissipate heat.
- 2. The bottom side area directly below the IC should a dedicated ground area. It should be directly connected to the thermal pad of the device using vias as shown. The ground area should be as large as practical. Additional internal layers can be dedicated as ground planes and connected to the vias as well.
- 3. Keep the input switching current loop as small as possible.
- 4. Keep the SW node as physically small and short as possible to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin of the device.
- 5. Keep analog and non-switching components away from switching components.
- 6. Make a single point connection from the signal ground to power ground.
- 7. Do not allow switching current to flow under the device.
- 8. Keep the pattern lines for VIN and PGND broad.
- 9. Exposed pad of device must be connected to PGND with solder.
- 10. VREG5 capacitor should be placed near the device, and connected PGND.
- 11. Output capacitor should be connected to a broad pattern of the PGND.
- 12. Voltage feedback loop should be as short as possible, and preferably with ground shield.
- 13. Lower resistor of the voltage divider which is connected to the VFB pin should be tied to SGND.
- 14. Providing sufficient via is preferable for VIN, SW and PGND connection.
- 15. PCB pattern for VIN, SW, and PGND should be as broad as possible.
- 16. VIN Capacitor should be placed as near as possible to the device.





Page

# **REVISION HISTORY**

| • | 已删除特性:轻负载下实现高效率的自动跳跃 Eco-mode™ | I | 1 |
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### PACKAGING INFORMATION

| Orderable Device | Status<br>(1) | Package Type | Package<br>Drawing | Pins | Package<br>Qty | Eco Plan<br>(2) | Lead finish/<br>Ball material<br>(6) | MSL Peak Temp<br>(3) | Op Temp (°C) | Device Marking<br>(4/5) | Samples |
|------------------|---------------|--------------|--------------------|------|----------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|---------|
| TPS54627DDA      | ACTIVE        | SO PowerPAD  | DDA                | 8    | 75             | RoHS & Green    | NIPDAU   SN                          | Level-2-260C-1 YEAR  | -40 to 85    | 54627                   | Samples |
| TPS54627DDAR     | ACTIVE        | SO PowerPAD  | DDA                | 8    | 2500           | RoHS & Green    | NIPDAU   SN                          | Level-2-260C-1 YEAR  | -40 to 85    | 54627                   | Samples |

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE OPTION ADDENDUM

11-Aug-2021

# TEXAS INSTRUMENTS

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18-Dec-2024

# TUBE



# - B - Alignment groove width

\*All dimensions are nominal

| Device      | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | Τ (μm) | B (mm) |
|-------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| TPS54627DDA | DDA          | HSOIC        | 8    | 75  | 508    | 7.77   | 2540   | NA     |
| TPS54627DDA | DDA          | HSOIC        | 8    | 75  | 517    | 7.87   | 635    | 4.25   |

# **GENERIC PACKAGE VIEW**

# **DDA 8**

# PowerPAD<sup>™</sup> SOIC - 1.7 mm max height PLASTIC SMALL OUTLINE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



# **DDA0008B**



# **PACKAGE OUTLINE**

# PowerPAD<sup>™</sup> SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



#### NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MS-012.



# DDA0008B

# **EXAMPLE BOARD LAYOUT**

# PowerPAD<sup>™</sup> SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.
- 10. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



# DDA0008B

# **EXAMPLE STENCIL DESIGN**

# PowerPAD<sup>™</sup> SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



DDA (R-PDSO-G8)

PowerPAD ™ PLASTIC SMALL-OUTLINE



- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. This package complies to JEDEC MS-012 variation BA

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# DDA (R-PDSO-G8)

# PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE

### THERMAL INFORMATION

This PowerPAD<sup> $\mathbb{N}$ </sup> package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206322-6/L 05/12

NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments



# DDA (R-PDSO-G8)

PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads. PowerPAD is a trademark of Texas Instruments.



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